

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	348945	257/\$.cccls. 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	102839	1 and (FET? or MISFET or MOSFET or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	330	2 and (first and second) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	4	3 and (SiO or (silicon near oxide)) and (TiO? or ((titanium or hafnium) near dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	771	1 and (dual or double or (thick and thin)) near (gate near (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	46	5 and (first and second) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	1047	(furukawa-ryoichi or sakai-satoshi or yamamoto-satoshi).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	0	7 and (first and second) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	18	7 and MISFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	173	(dual or double or (thick and thin)) near (gate near (oxide or dielectric)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	15	10 and (first and second) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	6	11 and (dielectric near constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L13	1195	(dual or double or (thick and thin)) near (gate near (oxide or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L14	5	13 and (SiO or (silicon near oxide)) and (TiO? or ((titanium or hafnium) near dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Comments
15	BRS	L15	50	13 and (first and second) near (gate near dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	BRS	L16	9	15 and (different or lower or higher) near (dielectric near constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	